



2N7002KDW

60V N-Channel Enhancement Mode MOSFET – ESD Protected

Voltage

60 V

Current

250mA

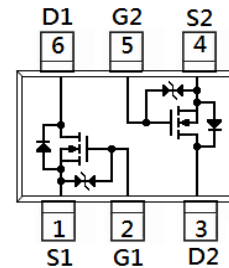
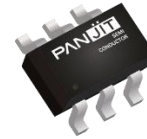
Features

- $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@500mA < 3\Omega$
- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_D@200mA < 4\Omega$
- Advanced Trench Process Technology
- High Density Cell Design For Ultra Low On-Resistance
- Very Low Leakage Current In Off Condition
- Specially Designed for Battery Operated Systems, Solid-State Relays Drivers: Relay, Displays, Memories, etc
- ESD Protected 2KV HBM
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : SOT-363 Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.006 grams

SOT-363



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	+20	
Continuous Drain Current	I_D	250	mA
Pulsed Drain Current	I_{DM}	1000	
Power Dissipation	$T_A=25^\circ\text{C}$	350	mW
	Derate above 25°C	4	mW/ $^\circ\text{C}$
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55~150	$^\circ\text{C}$
Typical Thermal Resistance - Junction to Ambient ^(Note 3)	$R_{\theta JA}$	357	$^\circ\text{C/W}$



2N7002KDW

Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =10uA	60	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	1	-	2.5	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =500mA	-	-	3	Ω
		V _{GS} =4.5V, I _D =200mA	-	-	4	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V	-	-	1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±10	
Forward Transconductance	g _{fs}	V _{DS} =15V, I _D =250mA	100	-	-	mS
Dynamic (Note 5)						
Total Gate Charge	Q _g	V _{DS} =15V, I _D =250mA, V _{GS} =5V (Note 1,2)	-	0.8	-	nC
Gate-Source Charge	Q _{gs}		-	0.35	-	
Gate-Drain Charge	Q _{gd}		-	0.2	-	
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f=1MHZ	-	35	-	pF
Output Capacitance	C _{oss}		-	13	-	
Reverse Transfer Capacitance	C _{rss}		-	8	-	
Turn-On Delay Time	t _{d(on)}	V _{DD} =30V, I _D =200mA, V _{GS} =10V, R _G =10Ω (Note 1,2)	-	2.7	-	ns
Turn-On Rise Time	t _r		-	19	-	
Turn-Off Delay Time	t _{d(off)}		-	15	-	
Turn-Off Fall Time	t _f		-	23	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I _S	---	-	-	250	mA
Diode Forward Voltage	V _{SD}	I _S =200mA, V _{GS} =0V	-	0.82	1.3	V

NOTES :

1. Pulse width ≤ 300us, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature typical characteristics.
3. R_{ΘJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
4. The maximum current rating is package limited.
5. Guaranteed by design, not subject to production testing.



2N7002KDW

TYPICAL CHARACTERISTIC CURVES

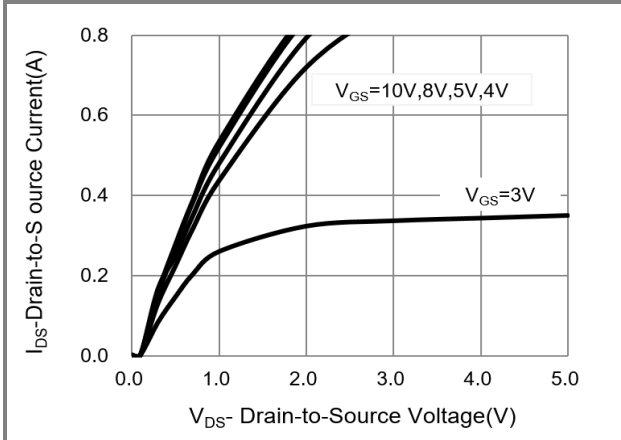


Fig.1 On-Region Characteristics

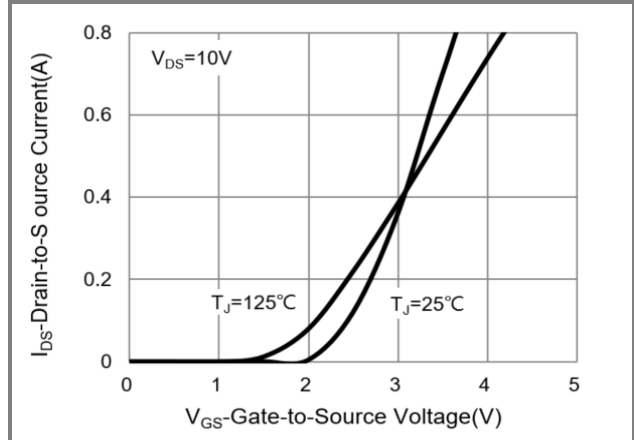


Fig.2 Transfer Characteristics

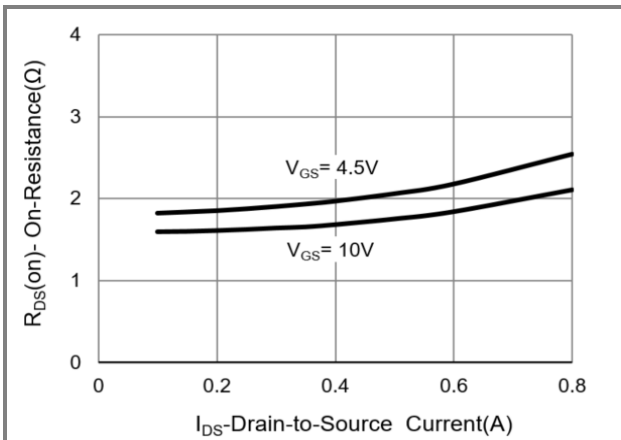


Fig.3 On-Resistance vs. Drain Current

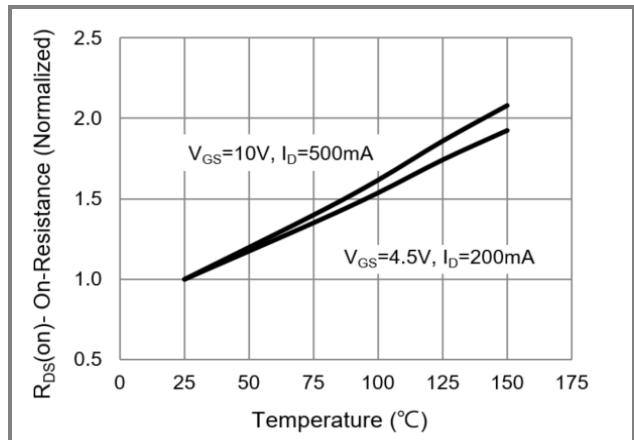


Fig.4 On-Resistance vs. Junction temperature

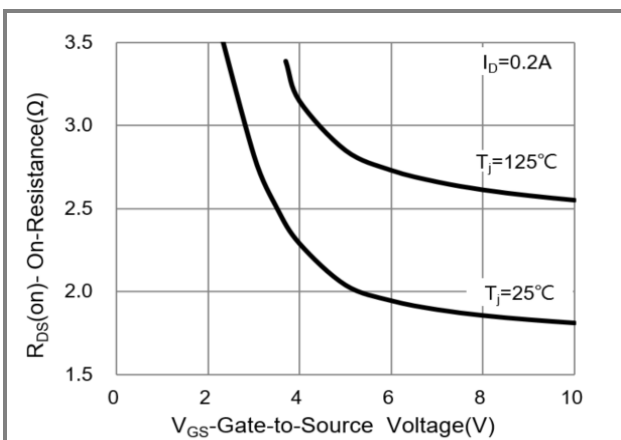


Fig.5 On-Resistance Variation with V_{GS}

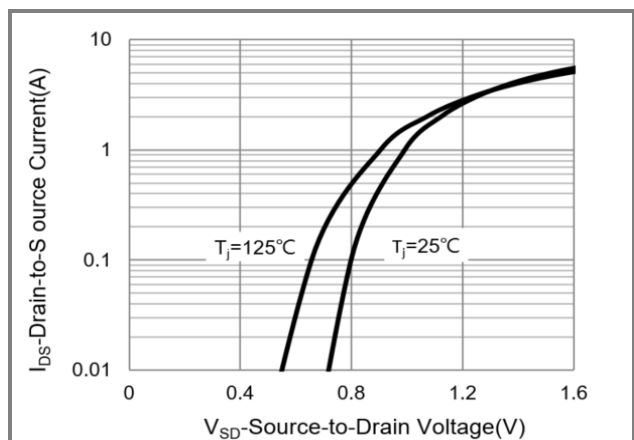


Fig.6 Body Diode Characteristics



2N7002KDW

TYPICAL CHARACTERISTIC CURVES

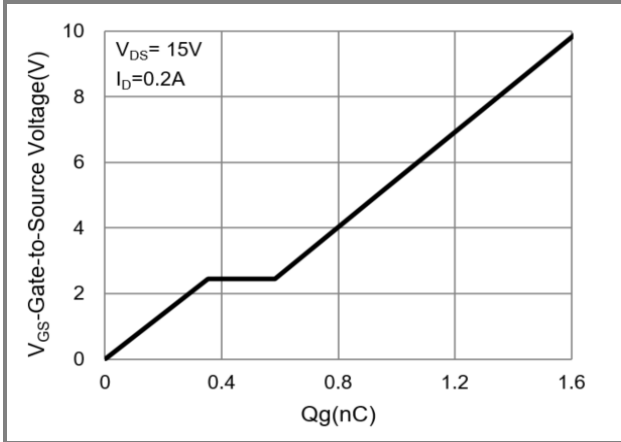


Fig.7 Gate-Charge Characteristics

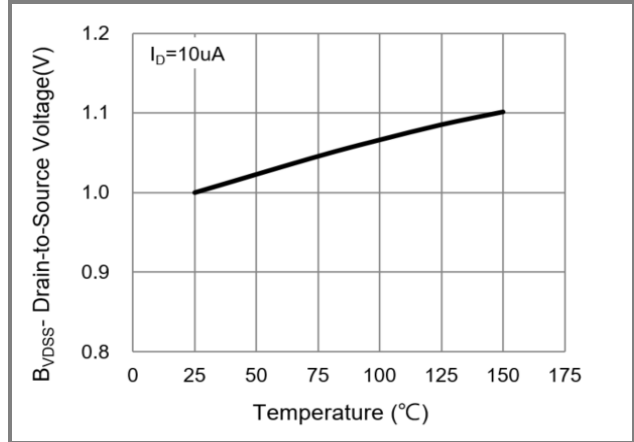


Fig.8 Breakdown Voltage Variation vs. Temperature

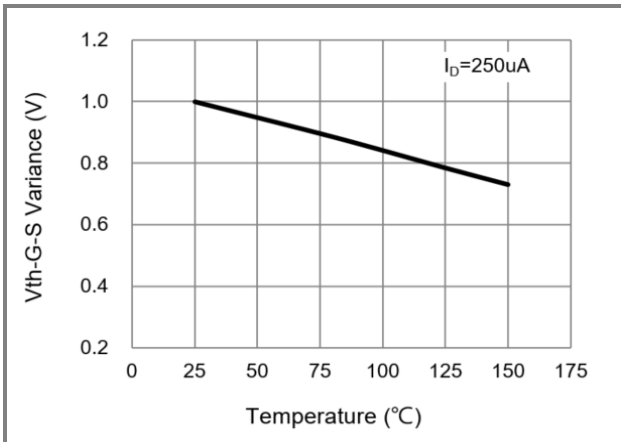


Fig.9 Threshold Voltage Variation with Temperature

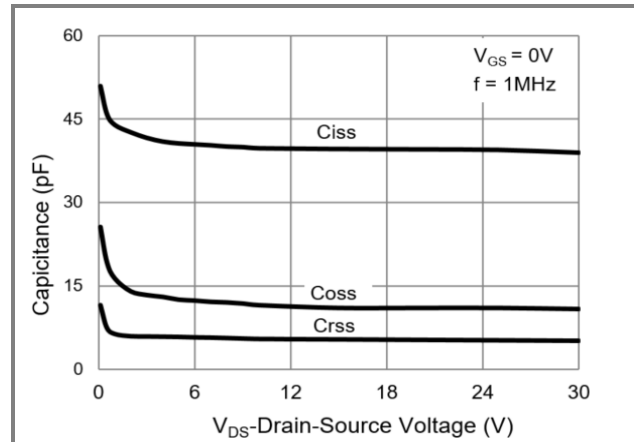


Fig.10 Capacitance vs. Drain-Source Voltage

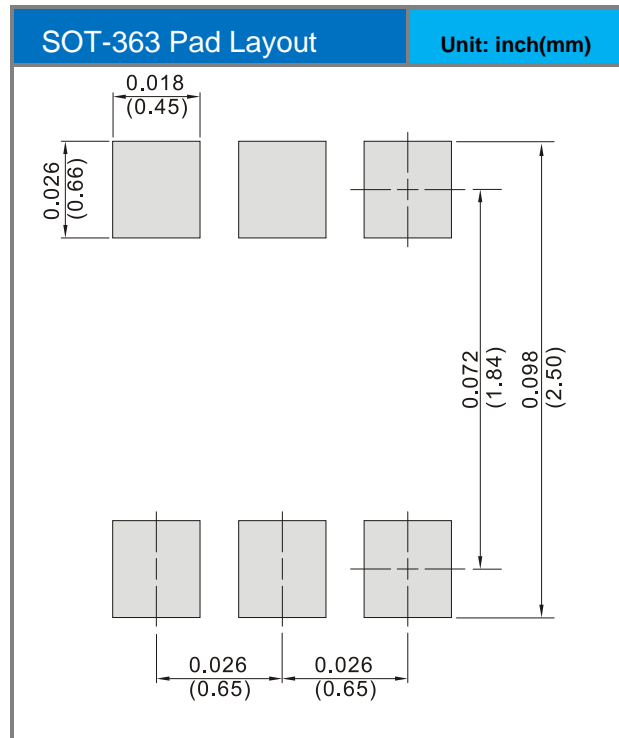
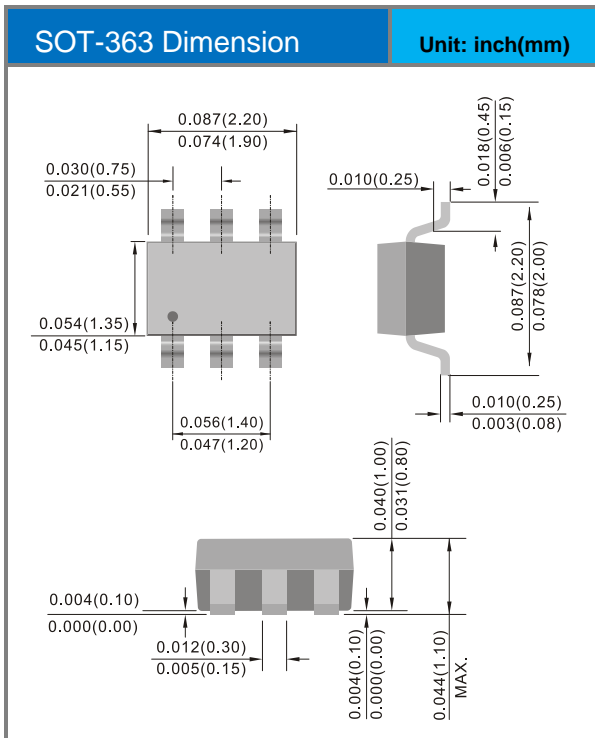


2N7002KDW

Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
2N7002KDW_R1_00501	SOT-363	3K pcs / 7" reel	K27	Halogen free RoHS compliant

Packaging Information & Mounting Pad Layout





2N7002KDW

Disclaimer

- Reproducing and modifying information of the document is prohibited without permission from Panjit International Inc..
- Panjit International Inc. reserves the rights to make changes of the content herein the document anytime without notification. Please refer to our website for the latest document.
- Panjit International Inc. disclaims any and all liability arising out of the application or use of any product including damages incidentally and consequentially occurred.
- Panjit International Inc. does not assume any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.
- Applications shown on the herein document are examples of standard use and operation. Customers are responsible in comprehending the suitable use in particular applications. Panjit International Inc. makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.
- The products shown herein are not designed and authorized for equipments requiring high level of reliability or relating to human life and for any applications concerning life-saving or life-sustaining, such as medical instruments, transportation equipment, aerospace machinery et cetera. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Panjit International Inc. for any damages resulting from such improper use or sale.
- Since Panjit uses lot number as the tracking base, please provide the lot number for tracking when complaining.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [MOSFET](#) category:

Click to view products by [Panjit](#) manufacturer:

Other Similar products are found below :

[IRFD120](#) [JANTX2N5237](#) [BUK455-60A/B](#) [MIC4420CM-TR](#) [VN1206L](#) [NDP4060](#) [SI4482DY](#) [IPS70R2K0CEAKMA1](#) [SQD23N06-31L-GE3](#)
[TK16J60W,S1VQ\(O](#) [2SK2614\(TE16L1,Q\)](#) [DMN1017UCP3-7](#) [DMN1053UCP4-7](#) [SQJ469EP-T1-GE3](#) [NTE2384](#) [DMC2700UDMQ-7](#)
[DMN2080UCB4-7](#) [DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [DMP22D4UFO-7B](#) [DMN1006UCA6-7](#) [DMN16M9UCA6-7](#)
[STF5N65M6](#) [IRF40H233XTMA1](#) [STU5N65M6](#) [DMN6022SSD-13](#) [DMN13M9UCA6-7](#) [DMTH10H4M6SPS-13](#) [DMN2990UFB-7B](#)
[IPB80P04P405ATMA2](#) [2N7002W-G](#) [MCAC30N06Y-TP](#) [MCQ7328-TP](#) [NTMC083NP10M5L](#) [NVMFS2D3P04M8LT1G](#) [BXP7N65D](#)
[BXP4N65F](#) [AOL1454G](#) [WMJ80N60C4](#) [BXP2N20L](#) [BXP2N65D](#) [BXT1150N10J](#) [BXT1700P06M](#) [TSM60NB380CP](#) [ROG](#) [RQ7L055BGTCR](#)
[DMNH15H110SK3-13](#) [SLF10N65ABV2](#) [BSO203SP](#) [BSO211P](#)